

IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-5. (Canceled)

6. (Currently Amended) A method of making a transistor on a substrate having a dielectric layer thereon comprising:
forming a gate structure overlying the dielectric layer, the dielectric layer including ~~gate structure~~ ~~having~~ a gate oxide layer ~~formed on the dielectric layer~~, a polysilicon layer formed on the gate oxide layer and a metal silicide layer formed on the polysilicon layer and a dielectric cap formed on the metal silicide layer, ~~the gate structure having~~ a first sidewall and a second sidewall[[,]] defining a first contact region, a second contact region and a channel region therebetween; and
forming first, second and third subregions within the contact regions, each subregion having a dopant concentration that is different from that of the other two subregions, wherein forming said subregions comprises:
introducing a first dopant into the substrate to form a first subregion, the first subregion being generally aligned with the sidewalls of the gate structure;
forming a first single thin layer sidewall spacer of dielectric material overlying the sidewalls, the first single thin layer sidewall spacer formed by depositing a thin conformal layer of dielectric material over the substrate and etching to a predetermined thickness over the sidewalls;
providing an annealing/oxidation step at an elevated temperature;
forming a second single layer sidewall spacer overlying the first single thin layer spacer, the second single layer sidewall spacer having a thickness greater than the first single thin layer sidewall spacer;
introducing a second dopant into the substrate to form the second subregion, the second subregion being generally aligned with the second single layer sidewall spacer;

reducing the thickness of the second single layer sidewall spacer to form a third sidewall spacer having a thickness intermediate the first and second sidewall spacers;
~~maintaining~~ maintaining the third sidewall spacer; and
introducing a third dopant into the substrate to form the third subregion, the third subregion being generally aligned with the third sidewall spacer.

7. (Previously Presented) The method of claim 6, wherein the first single thin layer sidewall spacer is anisotropically etched to a thickness of between about 50 and 150 Angstroms.

8. (Previously Presented) The method of claim 6, wherein the second single layer sidewall spacer is etched to a thickness of about 2 to 20 times the thickness of the first single thin layer sidewall spacer.

9. (Previously Presented) The method of claim 6, wherein the second single layer sidewall spacer is etched to a thickness of about 550 Angstroms.

10. (Previously Presented) The method of claim 6, wherein the first single thin layer sidewall spacer is formed of one of silicon nitride and silicon dioxide.